



IRF640 IRF640FP

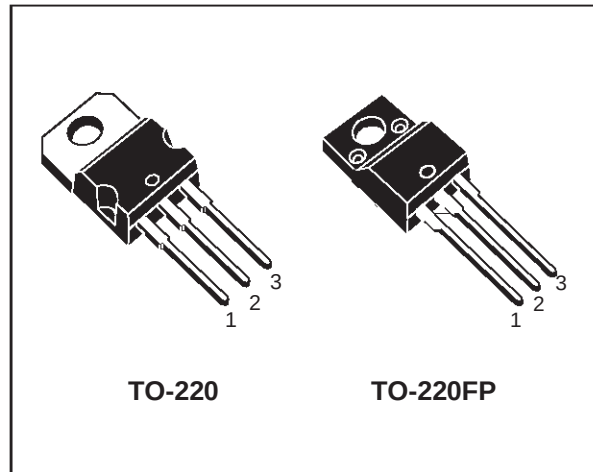
N - CHANNEL 200V - 0.150Ω - 18A - TO-220/FP MESH OVERLAY™ MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
IRF640	200 V	< 0.18 Ω	18 A
IRF640FP	200 V	< 0.18 Ω	18 A

- TYPICAL R_{DS(on)} = 0.150 Ω
- EXTREMELY HIGH dV/dt CAPABILITY
- VERY LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED

DESCRIPTION

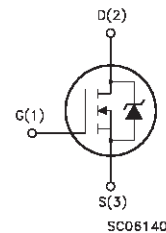
This power MOSFET is designed using the company's consolidated strip layout-based MESH OVERLAY™ process. This technology matches and improves the performances compared with standard parts from various sources.



APPLICATIONS

- HIGH CURRENT SWITCHING
- UNINTERRUPTIBLE POWER SUPPLY (UPS)
- DC/DC CONVERTERS FOR TELECOM, INDUSTRIAL, AND LIGHTING EQUIPMENT.

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		IRF640	IRF640FP	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	200		V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	200		V
V _{GS}	Gate-source Voltage	± 20		V
I _D	Drain Current (continuous) at T _c = 25 °C	18	18(**)	A
I _D	Drain Current (continuous) at T _c = 100 °C	11	11(**)	A
I _{DM} (●)	Drain Current (pulsed)	72	72	A
P _{tot}	Total Dissipation at T _c = 25 °C	125	40	W
	Derating Factor	1.0	0.32	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	5	5	V/ns
V _{ISO}	Insulation Withstand Voltage (DC)	—	2000	V
T _{stg}	Storage Temperature	-65 to 150		°C
T _j	Max. Operating Junction Temperature	150		°C

(●) Pulse width limited by safe operating area

(1) I_{SD} ≤ 18A, di/dt ≤ 300 A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}

First Digit of the Datecode Being Z or K Identifies Silicon Characterized in this Datasheet

(**) Limited only by Maximum Temperature Allowed

December 1998

THERMAL DATA

		TO-220	TO-220FP	
$R_{thj-case}$	Thermal Resistance Junction-case Max	1.0	3.12	$^{\circ}C/W$
$R_{thj-amb}$	Thermal Resistance Junction-ambient Max	62.5		$^{\circ}C/W$
$R_{thc-sink}$	Thermal Resistance Case-sink Typ	0.5		$^{\circ}C/W$
T_l	Maximum Lead Temperature For Soldering Purpose	300		$^{\circ}C$

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	18	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25^{\circ}C$, $I_D = I_{AR}$, $V_{DD} = 50$ V)	150	mJ

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250 \mu A$ $V_{GS} = 0$	200			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$ $T_c = 125^{\circ}C$			1 10	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20$ V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250 \mu A$	2	3	4	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10$ V $I_D = 9$ A		0.15	0.18	Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10$ V	18			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (*)$	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 9$ A	3	4		S
C_{iss}	Input Capacitance	$V_{DS} = 25$ V $f = 1$ MHz $V_{GS} = 0$		1200	1560	pF
C_{oss}	Output Capacitance			200	260	pF
C_{rss}	Reverse Transfer Capacitance			60	80	pF

ELECTRICAL CHARACTERISTICS (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 100\text{ V}$ $I_D = 9\text{ A}$		13	17	ns
t_r	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 3)		27	35	ns
Q_g	Total Gate Charge	$V_{DD} = 160\text{ V}$ $I_D = 18\text{ A}$ $V_{GS} = 10\text{ V}$		55	72	nC
Q_{gs}	Gate-Source Charge			10		nC
Q_{gd}	Gate-Drain Charge			21		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 160\text{ V}$ $I_D = 18\text{ A}$		21	27	ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		25	32	ns
t_c	Cross-over Time			50	65	ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				18	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				72	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 18\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 18\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 50\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, figure 5)		240		ns
Q_{rr}	Reverse Recovery Charge			1.8		μC
I_{RRM}	Reverse Recovery Current			15		A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

Fig. 1: Unclamped Inductive Load Test Circuit

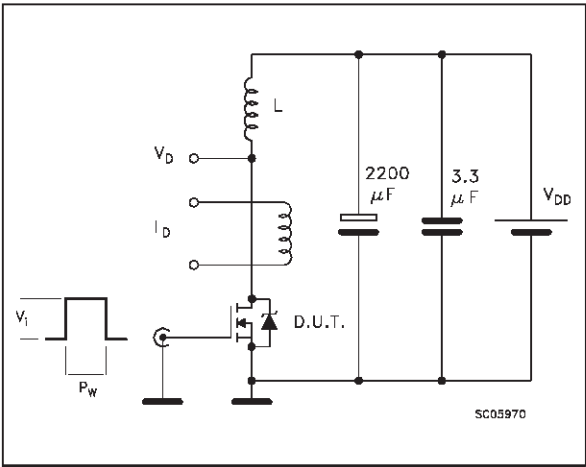


Fig. 2: Unclamped Inductive Waveform

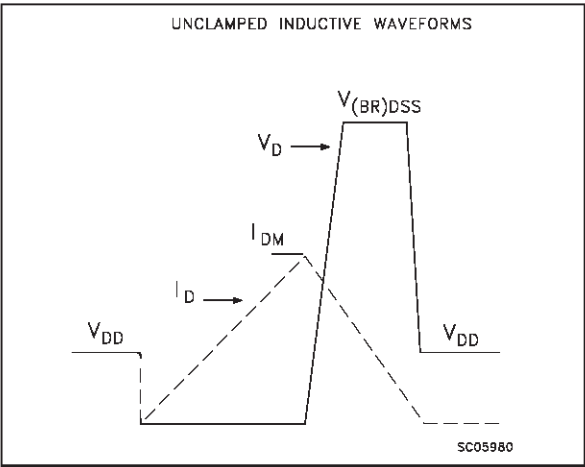


Fig. 3: Switching Times Test Circuits For Resistive Load

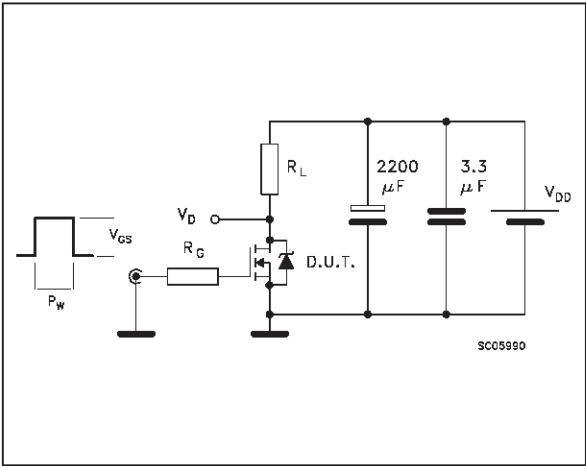


Fig. 4: Gate Charge test Circuit

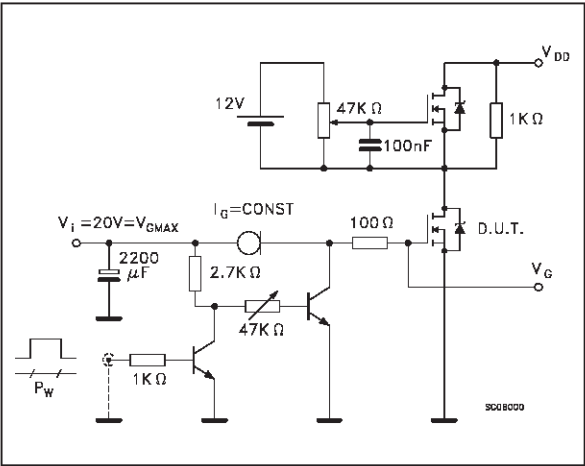
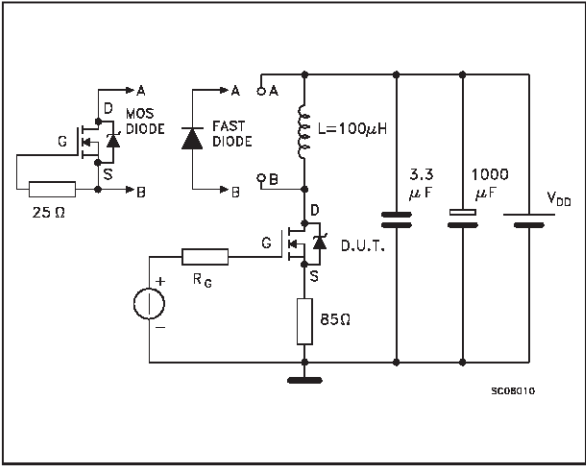
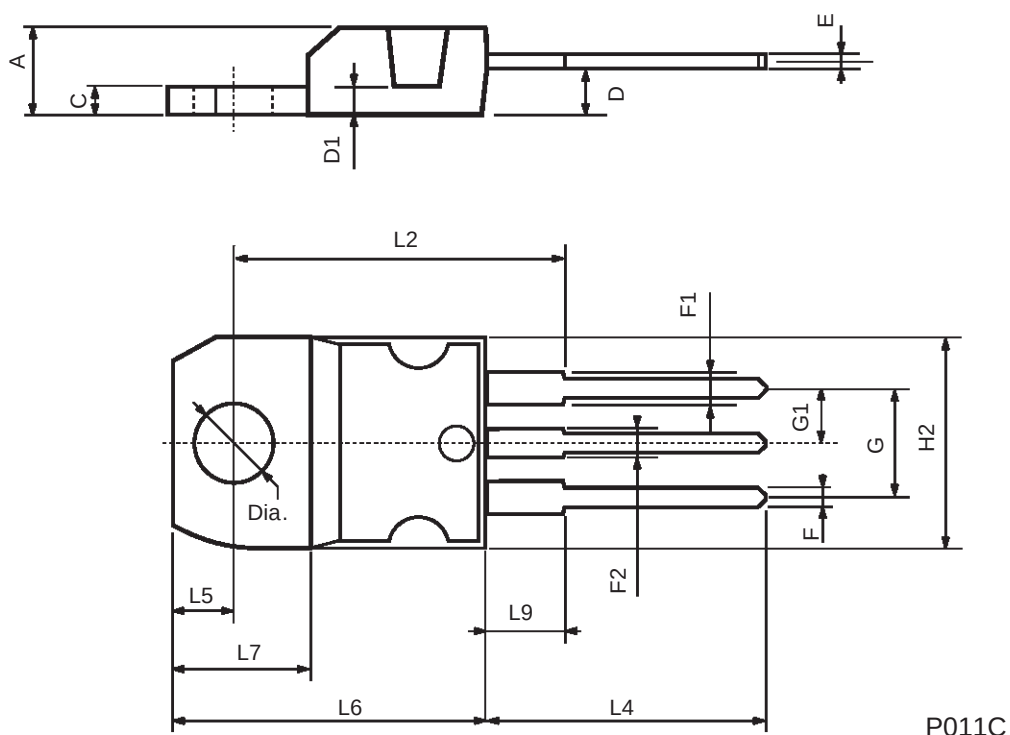


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-220 MECHANICAL DATA

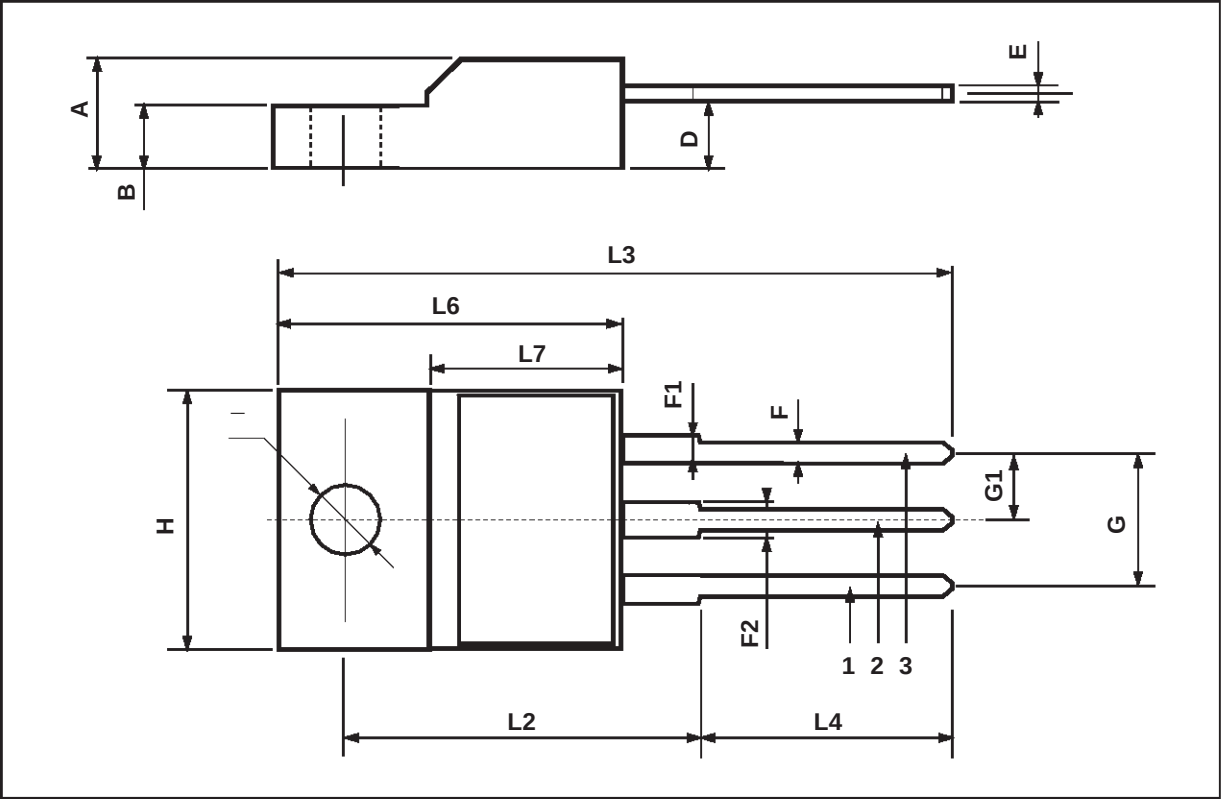
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



P011C

TO-220FP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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